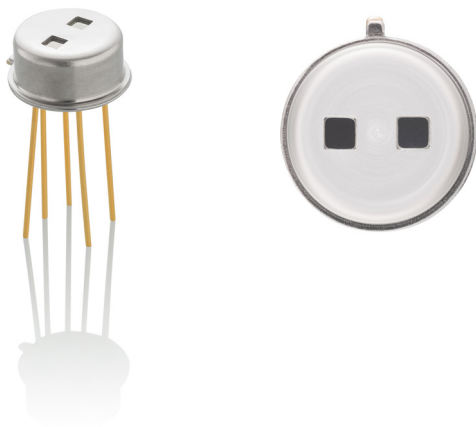


RTD120D

Silicon-Based Thermopile Detector 120 Dual

The RTD120D is a two-channel silicon-based thermopile detector in a TO-5 package. The device offers a low-cost solution with high output and fast response, with a time constant of 25ms with Nitrogen encapsulation gas.

Image Diagram



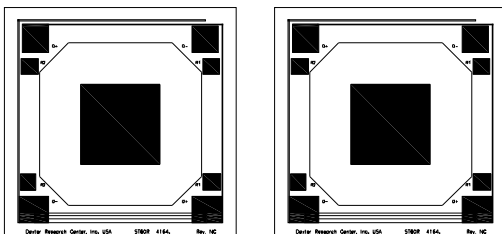
Features

- A two-channel silicon-based thermopile detector in a TO-5 package
- Five pin, 9.22mm TO-5 package
- Each small active area size is 1.2 × 1.2 mm
- Delivers a time constant of 25ms with Nitrogen encapsulation gas
- Very low Temperature Coefficient of Responsivity of -0.04%/°C
- Very short thermal shock response to ambient temperature change
- Internal 5% NTC chip thermistor provides ambient package temperature measurement
- Internal aperture precisely defines active area for applications with FOV and/or spot size requirements

Benefits

- Low cost with high sensitivity and high output

Detector Circuit Overlay



Applications

- Gas analysis
- Fire suppression
- Non-contact temperature sensors
- Horizon sensors
- Capnography

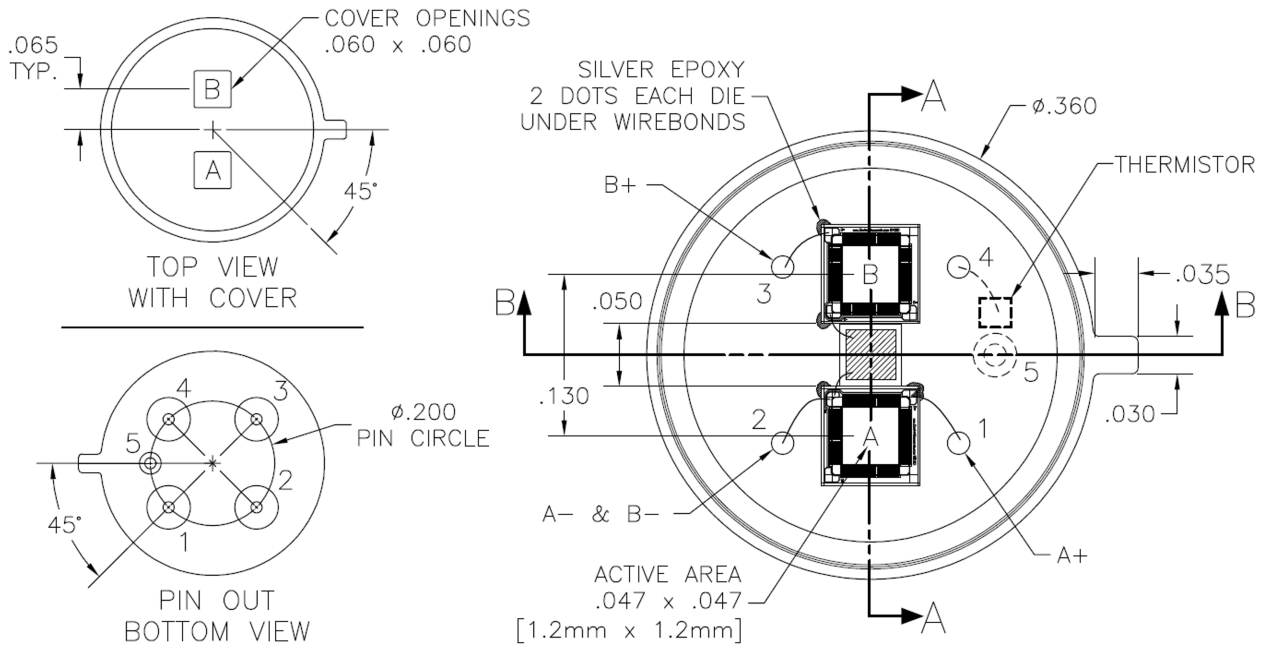
1. Specifications

Specifications apply at 23°C with KBr Window and Nitrogen encapsulating gas.

Symbol	Parameter	Min.	Typ.	Max.	Unit	Comments ^[1]
AA	Active Area size	1.2 × 1.2			mm	Hot junction size, per element.
A	Element Area	1.44			mm ²	
	Number of Junctions	80				Per element.
	Number of Channels	2				Per detector package.
V _s	Output Voltage	133	161	189	μV	DC, H = 330μW/cm ² [2]
SNR	Signal-to-Noise Ratio	3,067	4,197	5,225	√Hz	DC, SNR = V _s /V _n
R	Responsivity	28.0	33.9	39.8	V/W	DC, ℜ = V _s /HA [3]
R	Resistance	80	90	115	kΩ	Detector element
	Temperature Coefficient of ℜ		-0.04		%/°C	Best linear fit, 0° to 85°C [4]
	Temperature Coefficient of R		0.02		%/°C	Best fit, 0° to 85°C [4]
V _n	Noise Voltage	36.2	38.4	43.4	nV/√Hz	V _n ² = 4kTR
NEP	Noise Equivalent Power	0.91	1.13	1.55	nW/√Hz	DC, NEP = V _n HA/V _s [3]
D*	Detectivity	0.77	1.06	1.32	10 ⁸ cm√Hz/Ω	DC, D* = V _s / V _n H√A [3]
T	Time Constant		25		ms	Chopped, -3dB point [4]
FOV	Field of View	8°/60°			Degrees	For FOV description, see Package Outline Drawings
	Package Type	TO-5				Standard package hole size: 0.060" × 0.060"
M	Element Matching	25			%	ℳ = V _A -V _B /V _B [3]
	Element Separation	3.30			mm	Center to center
T _a	Operating Temperature	-50		+125	°C	
	Reference Filter, Central Wave Length		3.920		μm	Element A
	CO ₂ Filter, Central Wave Length		4.260		μm	Element B

1. General specifications: Flat spectral response from 100nm to > 100μm. Linear signal output from 10⁻⁶ to 0.1W/cm². Maximum incident radiance 0.1W/cm², damage threshold ≥ .5W/cm².
2. Test conditions: 500K Blackbody source; Detector active surface 10cm from 0.6513cm diameter Blackbody Aperture.
3. A is detector area in mm².
4. Parameter is not 100% tested. 90% of all units meet these specifications.

2. Package Outline Drawings



PIN	ELEMENT	DESCRIPTION	P/N
1	A+		
2	DETECTOR COMMON (A- & B-)		
3	B+		
4	OPTIONAL THERMISTOR		
5	CASE GROUND, OPTIONAL THERMISTOR		

Figure 1. Package Outline Drawings – Top View

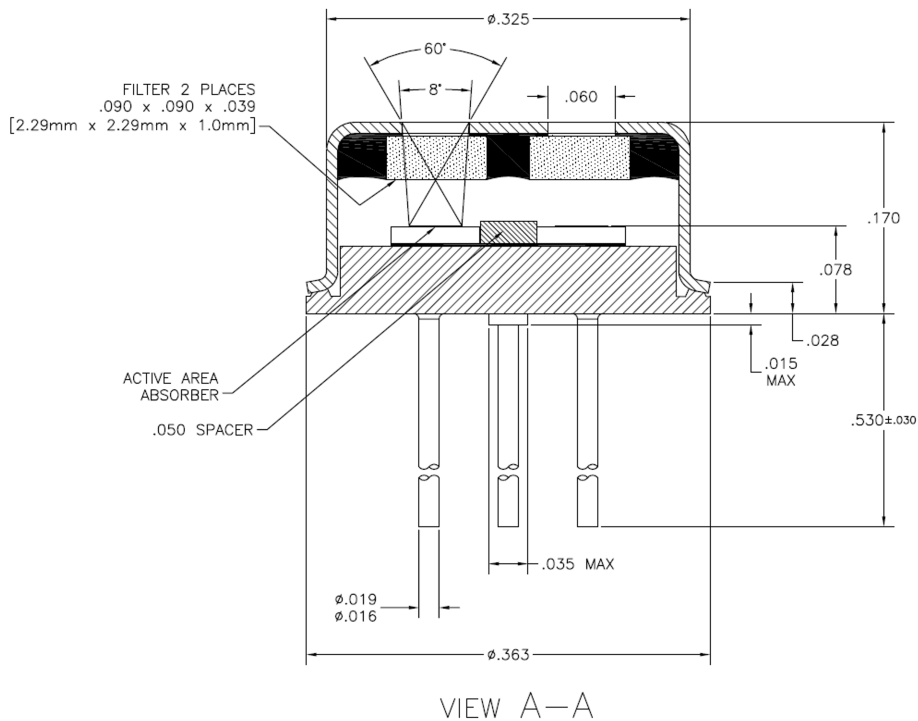


Figure 2. Package Outline Drawings – Side View

3. Ordering Information

Orderable Part Number	Package	Temperature	Carrier Type
RH5Z1222D20GZO#ADO	9.22mm TO-5 package	-50 to +125°C	Tray

4. Revision History

Revision	Date	Description
1.00	Aug 31, 2021	Initial release.

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